

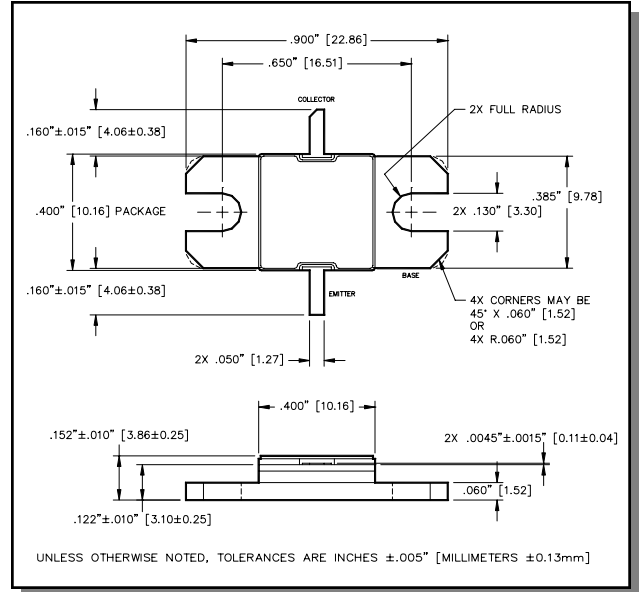
Radar Pulsed Power Transistor
55W, 1.2-1.4 GHz, 1ms Pulse, 10% Duty

M/A-COM Products
Released, 30 May 07

Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Outline Drawing



Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	58	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I_C	7.0	A
Power Dissipation @ +25°C	P_{TOT}	220	W
Storage Temperature	T_{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 120\text{mA}$		BV_{CES}	58	-	V
Collector-Emitter Leakage Current	$V_{CE} = 28\text{V}$		I_{CES}	-	6.0	mA
Thermal Resistance	$V_{CC} = 28\text{V}$, $P_{in} = 12\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$R_{TH(JC)}$	-	0.8	°C/W
Output Power	$V_{CC} = 28\text{V}$, $P_{in} = 12\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	P_{OUT}	55	-	W
Power Gain	$V_{CC} = 28\text{V}$, $P_{in} = 12\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	G_P	6.6	-	dB
Collector Efficiency	$V_{CC} = 28\text{V}$, $P_{in} = 12\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	η_C	50	-	%
Input Return Loss	$V_{CC} = 28\text{V}$, $P_{in} = 12\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	RL	-	-10	dB
Load Mismatch Tolerance	$V_{CC} = 28\text{V}$, $P_{in} = 12\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	VSWR-T	-	3:1	-
Load Mismatch Stability	$V_{CC} = 28\text{V}$, $P_{in} = 12\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	VSWR-S	-	1.5:1	-

